

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

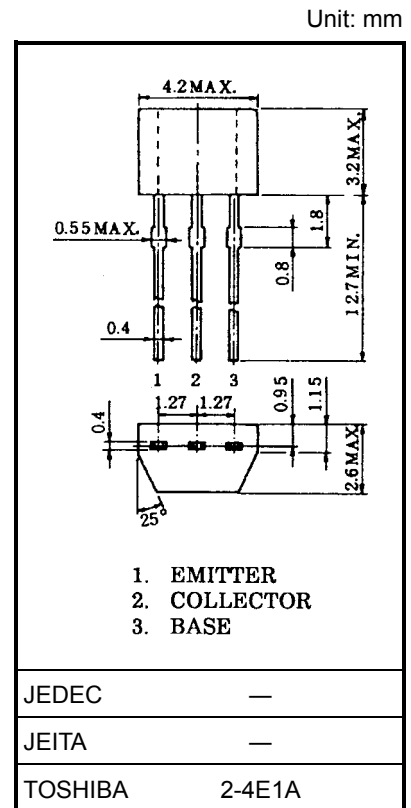
# 2SC2458

## Audio Amplifier Applications

- High current capability:  $I_C = 150 \text{ mA (max)}$
- High DC current gain:  $h_{FE} = 70\sim700$
- Excellent  $h_{FE}$  linearity:  $h_{FE} (I_C = 0.1 \text{ mA})/h_{FE} (I_C = 2 \text{ mA}) = 0.95 \text{ (typ.)}$
- Low noise:  $NF (2) = 1\text{dB (typ.)}, 10\text{dB (max)}$
- Complementary to 2SA1048.
- Small package.

## Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	150	mA
Base current	$I_B$	50	mA
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55~125	$^\circ\text{C}$

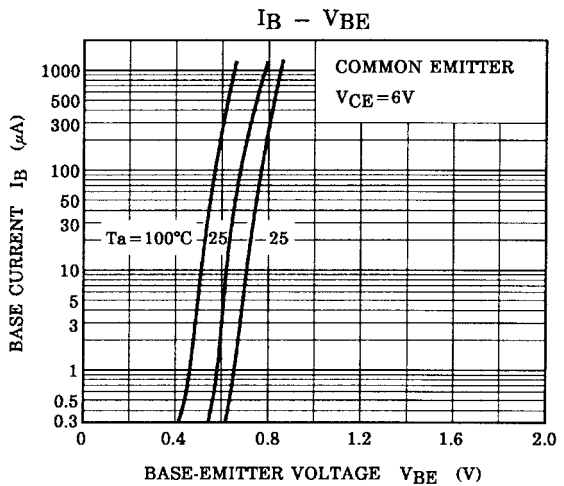
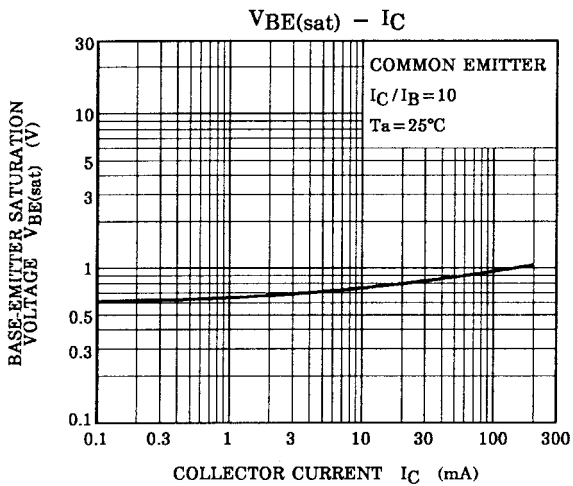
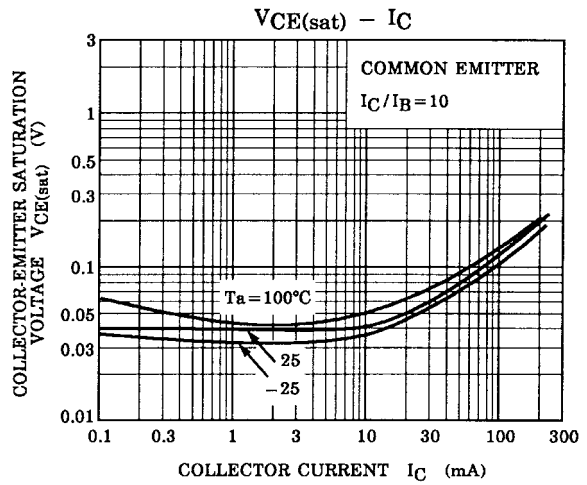
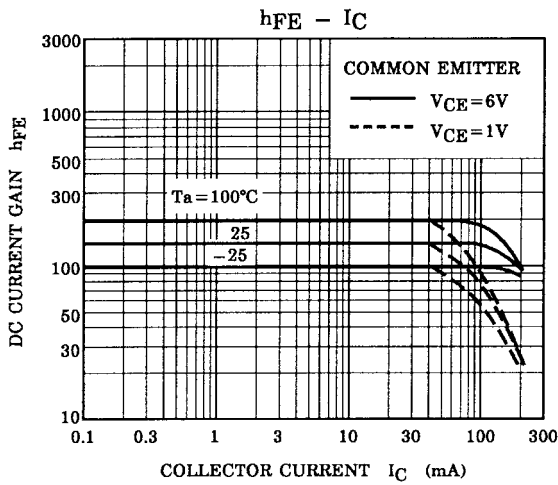
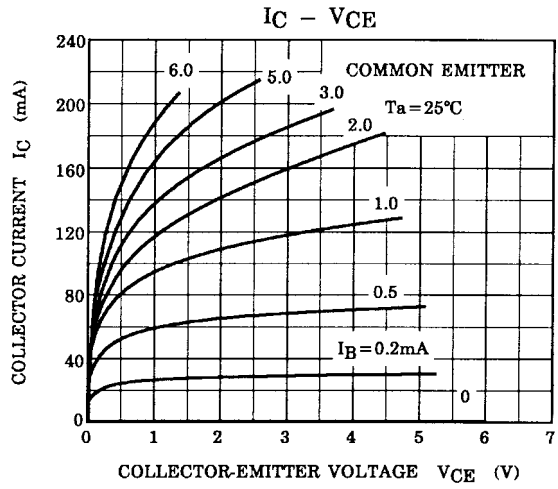
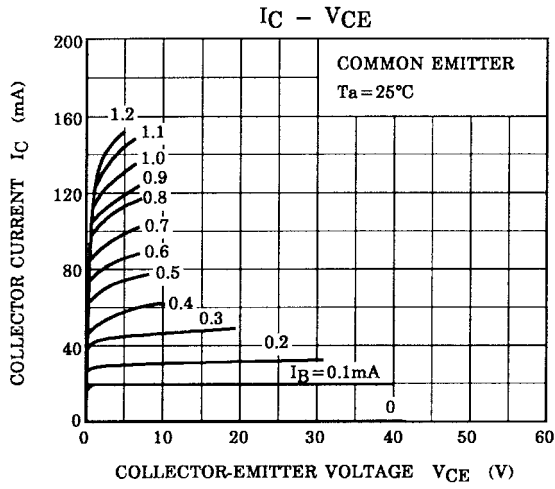


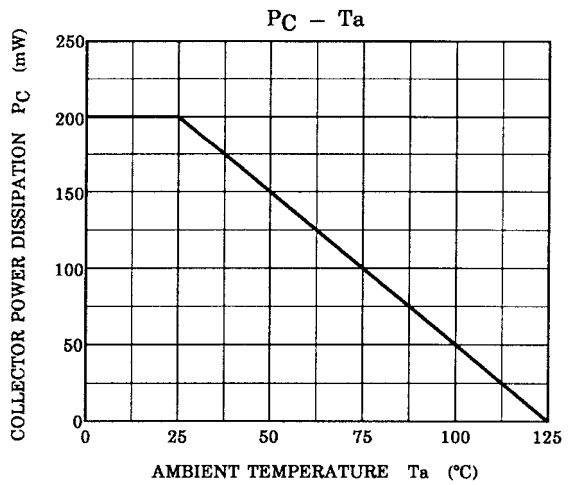
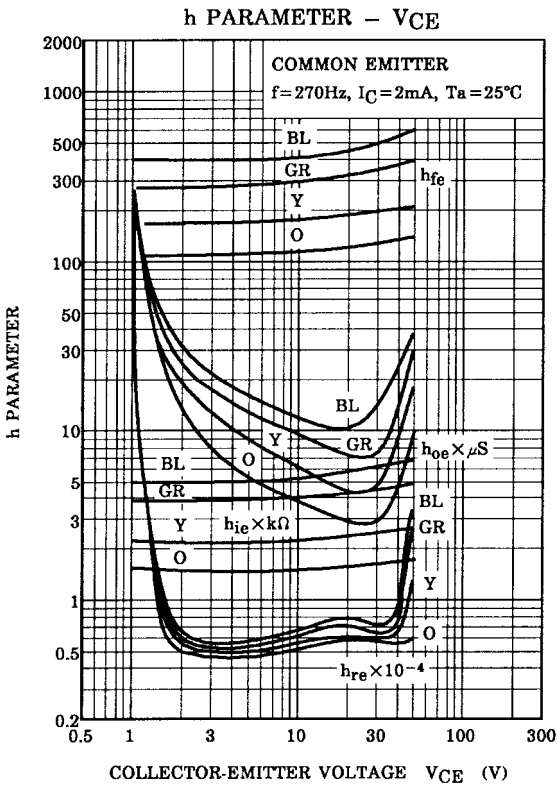
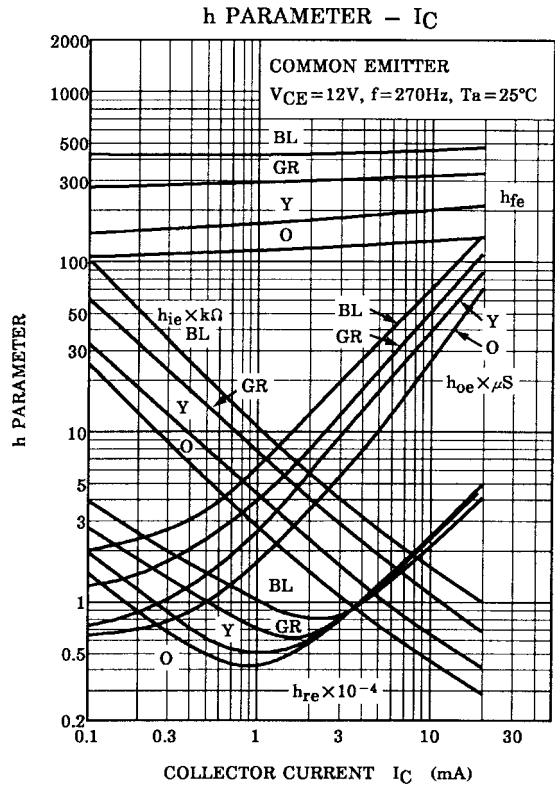
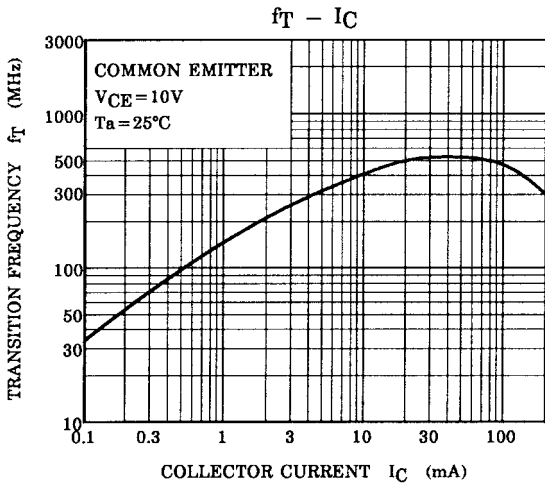
Weight: 0.13 g (typ.)

## Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_E = 0$	—	—	0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5 \text{ V}, I_C = 0$	—	—	0.1	$\mu\text{A}$
DC current gain	$h_{FE}$ (Note)	$V_{CE} = 6 \text{ V}, I_C = 2 \text{ mA}$	70	—	700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$	—	0.1	0.25	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_C = 1 \text{ mA}$	80	—	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	—	2.0	3.5	pF
Noise figure	NF	$V_{CE} = 6 \text{ V}, I_C = 0.1 \text{ mA}, f = 1 \text{ kHz}, R_g = 10 \text{ k}\Omega$	—	1.0	10	dB

Note:  $h_{FE}$  classification O: 70~140, Y: 120~240, GR: 200~400, BL: 350~700





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